

FEATURES

- \varnothing 11.28 mm active area
- Low series resistance
- Low dark current
- High sensitivity

DESCRIPTION

100.0 mm² Low Series Resistance Photodiode with P on N construction. Surface mount packaged with clear epoxy encapsulant.

APPLICATIONS

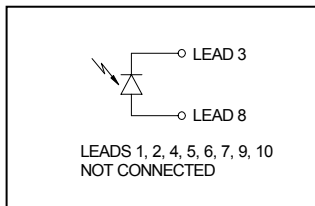
- Low light level sensing



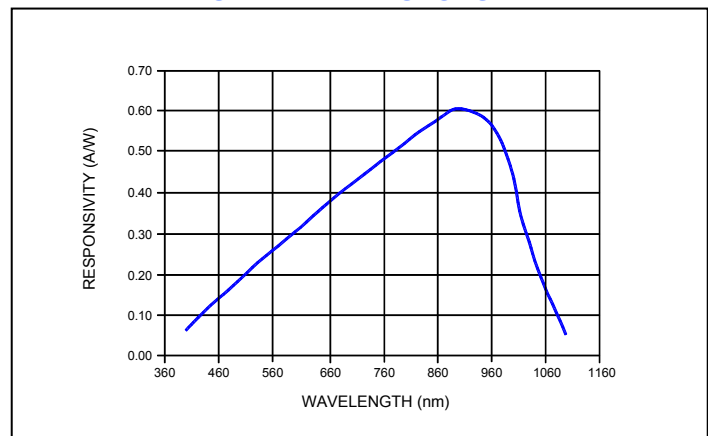
ABSOLUTE MAXIMUM RATING

SYMBOL	PARAMETER	MIN	MAX	UNITS
T _{STG}	Storage Temp	-20	+80	°C
T _{OP}	Operating Temp	-20	+60	°C
V _{R(OP)}	Reverse Operating Voltage	-	50	V
I _(PEAK)	Peak DC Current	-	10	mA

SCHEMATIC



SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS @ 22° C

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
R _{SH}	Shunt Resistance	V _R = ±10 mV	---	10	---	MΩ
I _D	Dark Current	V _R = 10 V	---	2.0	---	nA
C	Capacitance	V _R = 0 V;	---	2.0	---	nF
	Responsivity	V _R = 0 V; λ = 900 nm	---	0.60	---	A/W
NEP	Noise Equivalent Power	V _R = 10 V; λ = 900 nm; R _L = 50 Ω	---	5.0 × 10 ⁻¹⁴	---	W/Hz ^{1/2}
V _{BR}	Breakdown Voltage	I _R = 10 μA	100	---	---	V
t _r	Rise Time	V _R = 10 V; λ = 850 nm; R _L = 50 Ω	---	500	---	ns

Disclaimer: Due to our policy of continued development, specifications are subject to change without notice. Package is not suitable for reflow soldering.

USA:

Pacific Silicon Sensor, Inc.
5700 Corsa Avenue, #105
Westlake Village, CA 91362 USA
Phone (818) 706-3400
Fax (818) 889-7053
Email: sales@pacific-sensor.com
www.pacific-sensor.com

International sales:

Silicon Sensor International AG
Peter-Behrens-Str. 15
D-12459 Berlin, Germany
Phone +49 (0)30-63 99 23 10
Fax +49 (0)30-63 99 23 33
Email: sales@silicon-sensor.de
www.silicon-sensor.de